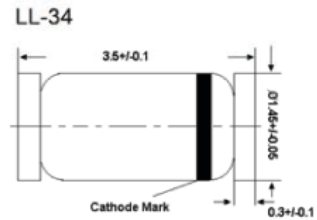


## Silicon Epitaxial Planar Switching Diode

### Applications

- High-speed switching



Glass case MiniMELF  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	$V_{RRM}$	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	1 4	A
		$t = 1\text{ s}$ $t = 1\text{ }\mu\text{s}$	
Power Dissipation	$P_{tot}$	500	mW
Operating Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 175	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 5\text{ }\mu\text{A}$	$V_R$	75	-	V
Forward Voltage at $I_F = 0.1\text{ mA}$ at $I_F = 0.25\text{ mA}$ at $I_F = 1\text{ mA}$ at $I_F = 2\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 20\text{ mA}$	$V_F$	0.45 0.49 0.55 0.6 0.69 0.72	0.51 0.55 0.61 0.67 0.76 0.86	V
Reverse Current at $V_R = 50\text{ V}$	$I_R$	-	50	nA
Total Capacitance at $V_R = 0$ , $f = 1\text{ MHz}$	$C_T$	-	2	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ , $V_R = 6\text{ V}$ , $R_L = 100\text{ }\Omega$ , $I_{rr} = 1\text{ mA}$	$t_{rr1}$	-	2	ns
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$ , $R_L = 100\text{ }\Omega$ , $I_{rr} = 1\text{ mA}$	$t_{rr2}$	-	4	ns